

Final datasheet

IHV-B Module with Trench/Fieldstop IGBT4 and emitter controlled 4 diode

Features

- Electrical features
 - $V_{CES} = 4500\text{ V}$
 - $I_{C\text{ nom}} = 1200\text{ A} / I_{CRM} = 2400\text{ A}$
 - High DC stability
 - High dynamic robustness
 - High short-circuit capability
 - Low $V_{CE,sat}$
 - Trench IGBT 4
 - $V_{CE,sat}$ with positive temperature coefficient
- Mechanical features
 - Package with CTI > 600
 - Standard housing
 - AlSiC base plate for increased thermal cycling capability
 - IHV-B housing
 - Isolated base plate



Potential applications

- High-power converters
- Medium-voltage converters
- Power transmission and distribution

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

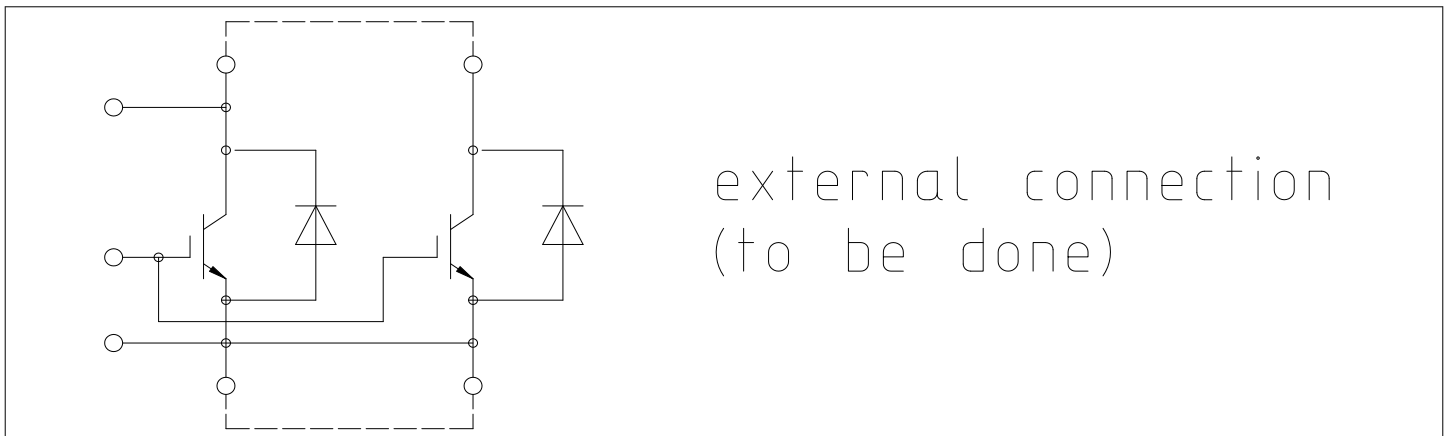


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1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50$ Hz, $t = 1$ min	6.0	kV
Partial discharge extinction voltage	V_{isol}	RMS, $f = 50$ Hz, $Q_{PD} \leq 10$ pC	3.5	kV
DC stability	$V_{CE(D)}$	$T_{vj} = 25$ °C, 100 Fit	2900	V
Material of module baseplate			AlSiC	
Comparative tracking index	CTI		> 600	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Stray inductance module	L_{sCE}			9		nH	
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_C = 25$ °C, per switch		0.12		mΩ	
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C = 25$ °C, per switch		0.14		mΩ	
Storage temperature	T_{stg}		-40		150	°C	
Mounting torque for module mounting	M	- Mounting according to valid application note	M6, Screw	4.25		5.75	Nm
Terminal connection torque	M	- Mounting according to valid application note	M4, Screw	1.8		2.1	Nm
			M8, Screw	8		10	
Weight	G			800		g	

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	V_{CES}		$T_{vj} = -40$ °C	4300	V
			$T_{vj} = 150$ °C	4500	
Continuous DC collector current	I_{CDC}	$T_{vj\ max} = 150$ °C	$T_C = 100$ °C	1200	A
Repetitive peak collector current	I_{CRM}	t_p limited by $T_{vj\ op}$		2400	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 1200\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		2.35	2.80	V
			$T_{vj} = 125\ ^\circ C$		2.85	3.40	
			$T_{vj} = 150\ ^\circ C$		2.95	3.50	
Gate threshold voltage	V_{Geth}	$I_C = 99\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.50	6.00	6.50	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CC} = 2800\ V, T_{vj} = 25\ ^\circ C$			31		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			0.19		Ω
Input capacitance	C_{ies}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			198		nF
Reverse transfer capacitance	C_{res}	$f = 100\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			3.6		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 4500\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			5	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				400	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 1200\ A, V_{CC} = 2800\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.1\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.260		μs
			$T_{vj} = 125\ ^\circ C$		0.290		
			$T_{vj} = 150\ ^\circ C$		0.310		
Rise time (inductive load)	t_r	$I_C = 1200\ A, V_{CC} = 2800\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.1\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.210		μs
			$T_{vj} = 125\ ^\circ C$		0.230		
			$T_{vj} = 150\ ^\circ C$		0.230		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 1200\ A, V_{CC} = 2800\ V, V_{GE} = \pm 15\ V, R_{Goff} = 7\ \Omega$	$T_{vj} = 25\ ^\circ C$		6.600		μs
			$T_{vj} = 125\ ^\circ C$		6.950		
			$T_{vj} = 150\ ^\circ C$		7.050		
Fall time (inductive load)	t_f	$I_C = 1200\ A, V_{CC} = 2800\ V, V_{GE} = \pm 15\ V, R_{Goff} = 7\ \Omega$	$T_{vj} = 25\ ^\circ C$		1.150		μs
			$T_{vj} = 125\ ^\circ C$		2.150		
			$T_{vj} = 150\ ^\circ C$		2.450		
Turn-on time (resistive load)	t_{on_R}	$I_C = 500\ A, V_{CC} = 2000\ V, V_{GE} = \pm 15\ V, R_{Gon} = 1.1\ \Omega$	$T_{vj} = 25\ ^\circ C$	0.98			μs
Turn-on energy loss per pulse	E_{on}	$I_C = 1200\ A, V_{CC} = 2800\ V, L_\sigma = 110\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 1.1\ \Omega, di/dt = 4350\ A/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		3850		mJ
			$T_{vj} = 125\ ^\circ C$		5400		
			$T_{vj} = 150\ ^\circ C$		6050		
Turn-off energy loss per pulse	E_{off}	$I_C = 1200\ A, V_{CC} = 2800\ V, L_\sigma = 110\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 7\ \Omega, dv/dt = 1250\ V/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		4700		mJ
			$T_{vj} = 125\ ^\circ C$		6000		
			$T_{vj} = 150\ ^\circ C$		6450		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
SC data	I_{SC}	$V_{GE} = 15 \text{ V}$, $V_{CC} = 3000 \text{ V}$, $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_p \leq 10 \mu\text{s}$, $T_{vj} = 150 \text{ }^\circ\text{C}$		5400		A
Thermal resistance, junction to case	R_{thJC}	per IGBT			10.8	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		5.40		K/kW
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		150	$^\circ\text{C}$

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = -40 \text{ }^\circ\text{C}$	4300		V
			$T_{vj} = 150 \text{ }^\circ\text{C}$	4500		
Continuous DC forward current	I_F			1200		A
Repetitive peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$		2400		A
I^2t - value	I^2t	$t_p = 10 \text{ ms}$, $V_R = 0 \text{ V}$	$T_{vj} = 125 \text{ }^\circ\text{C}$	415		kA ² s
			$T_{vj} = 150 \text{ }^\circ\text{C}$	380		
Maximum power dissipation	P_{RQM}		$T_{vj} = 150 \text{ }^\circ\text{C}$	2650		kW
Minimum turn-on time	t_{onmin}			10		μs

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 1200 \text{ A}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		2.60	3.05	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$		2.50	2.95	
			$T_{vj} = 150 \text{ }^\circ\text{C}$		2.45	2.90	
Peak reverse recovery current	I_{RM}	$V_{CC} = 2800 \text{ V}$, $I_F = 1200 \text{ A}$, $V_{GE} = -15 \text{ V}$, $-di_F/dt = 4350 \text{ A}/\mu\text{s}$ ($T_{vj} = 150 \text{ }^\circ\text{C}$)	$T_{vj} = 25 \text{ }^\circ\text{C}$		1600		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$		1750		
			$T_{vj} = 150 \text{ }^\circ\text{C}$		1750		

(table continues...)

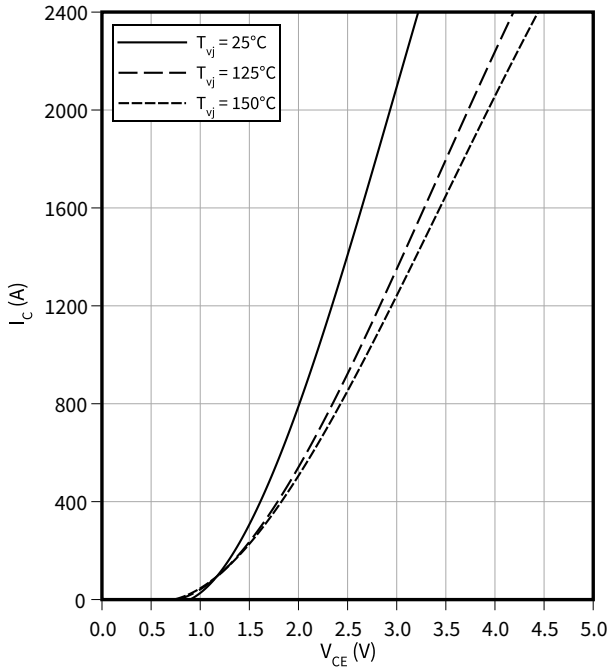
Table 6 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Recovered charge	Q_r	$V_{CC} = 2800 \text{ V}, I_F = 1200 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 4350 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$	1050		μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$	2050		
			$T_{vj} = 150 \text{ }^\circ\text{C}$	2400		
Reverse recovery energy	E_{rec}	$V_{CC} = 2800 \text{ V}, I_F = 1200 \text{ A}, V_{GE} = -15 \text{ V}, -di_F/dt = 4350 \text{ A}/\mu\text{s} (T_{vj} = 150 \text{ }^\circ\text{C})$	$T_{vj} = 25 \text{ }^\circ\text{C}$	1550		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	3450		
			$T_{vj} = 150 \text{ }^\circ\text{C}$	4050		
Thermal resistance, junction to case	R_{thJC}	per diode			19.1	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1 \text{ W}/(\text{m}\cdot\text{K})$		7.95		K/kW
Temperature under switching conditions	T_{vjop}		-40		150	$^\circ\text{C}$

4 Characteristics diagrams

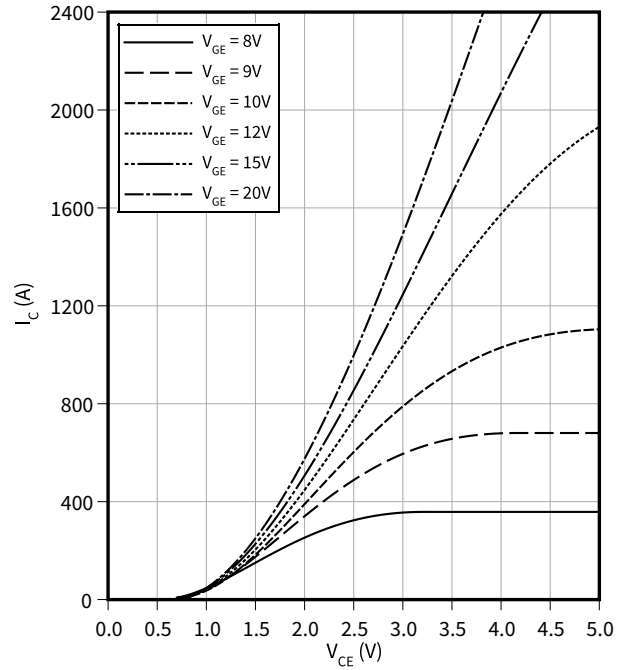
Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $V_{GE} = 15\text{ V}$



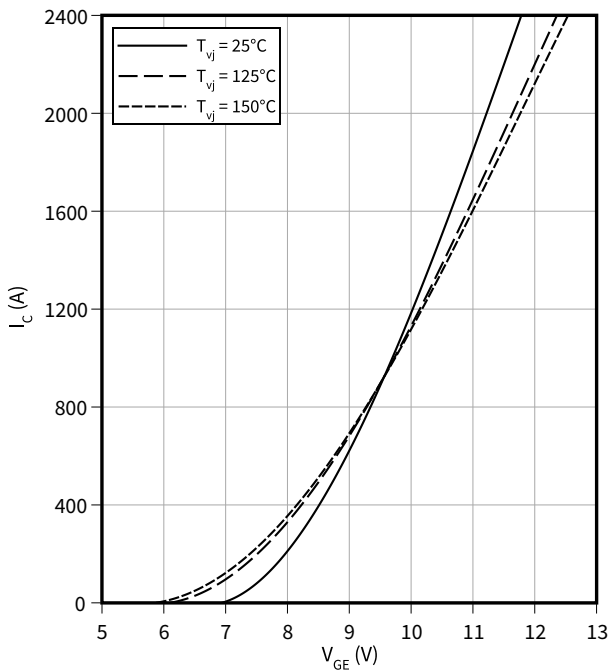
Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$
 $T_{vj} = 150\text{ °C}$



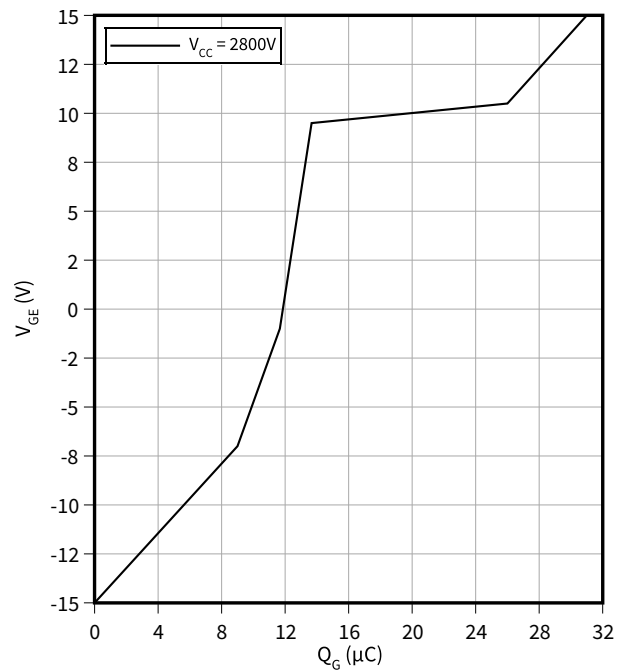
Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



Gate charge characteristic (typical), IGBT, Inverter

$V_{GE} = f(Q_G)$
 $I_C = 1200\text{ A}, T_{vj} = 25\text{ °C}$

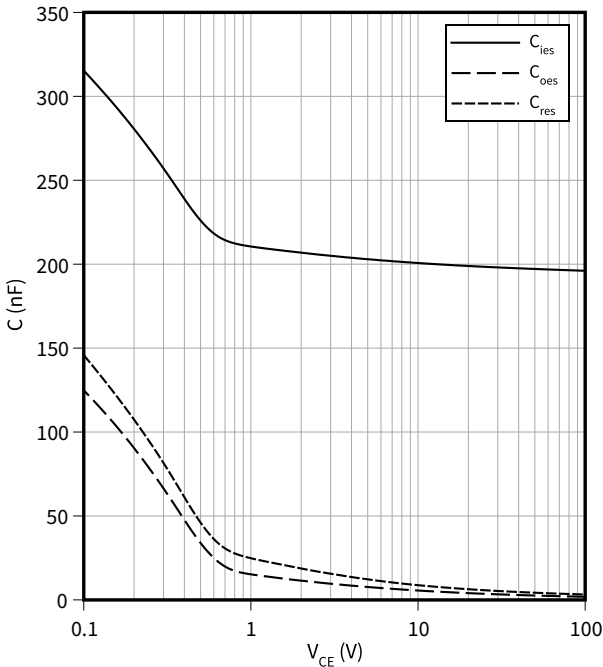


4 Characteristics diagrams

Capacity characteristic (typical), IGBT, Inverter

$C = f(V_{CE})$

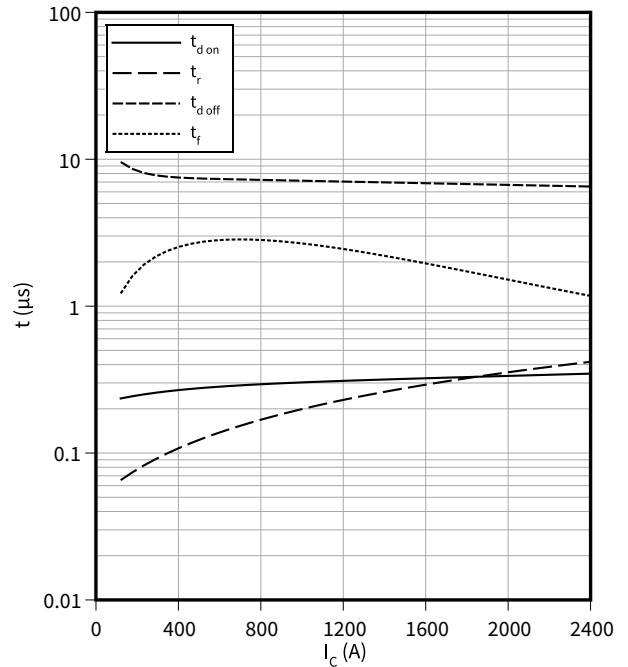
$f = 100 \text{ kHz}, V_{GE} = 0 \text{ V}, T_{vj} = 25 \text{ }^\circ\text{C}$



Switching times (typical), IGBT, Inverter

$t = f(I_C)$

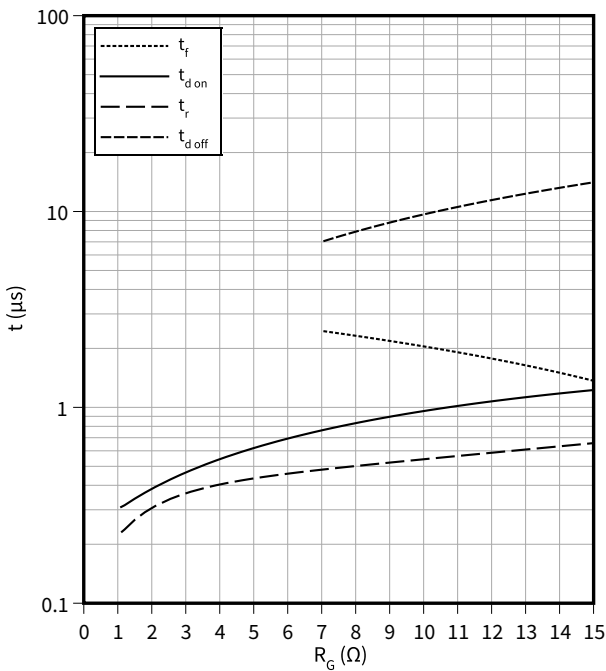
$R_{Goff} = 7 \text{ } \Omega, R_{Gon} = 1.1 \text{ } \Omega, V_{GE} = \pm 15 \text{ V}, V_{CC} = 2800 \text{ V}, T_{vj} = 150 \text{ }^\circ\text{C}$



Switching times (typical), IGBT, Inverter

$t = f(R_G)$

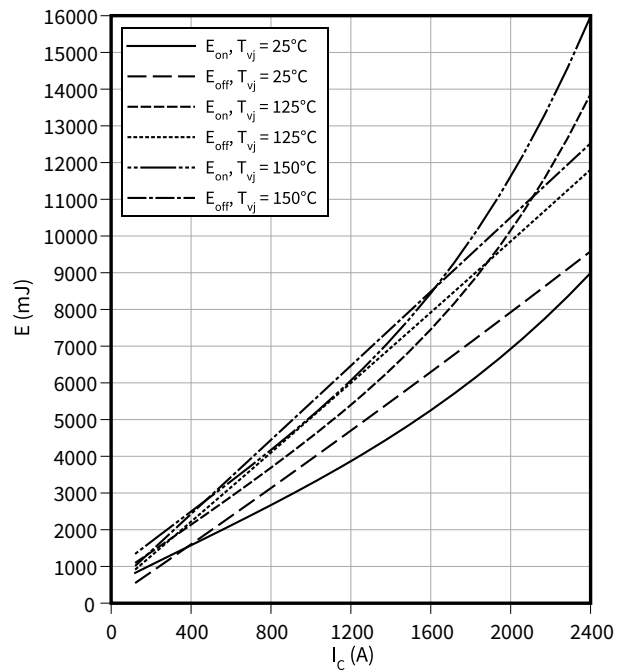
$V_{GE} = \pm 15 \text{ V}, I_C = 1200 \text{ A}, V_{CC} = 2800 \text{ V}, T_{vj} = 150 \text{ }^\circ\text{C}$



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

$R_{Goff} = 7 \text{ } \Omega, R_{Gon} = 1.1 \text{ } \Omega, V_{GE} = \pm 15 \text{ V}, V_{CC} = 2800 \text{ V}$

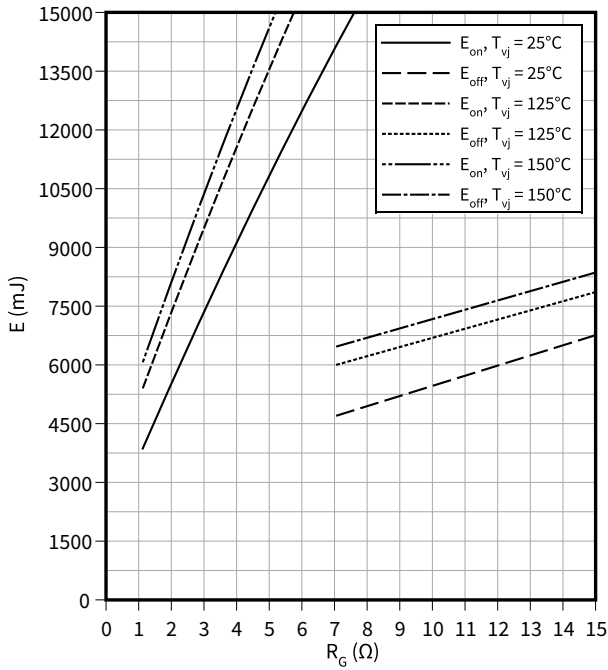


4 Characteristics diagrams

Switching losses (typical), IGBT, Inverter

$E = f(R_G)$

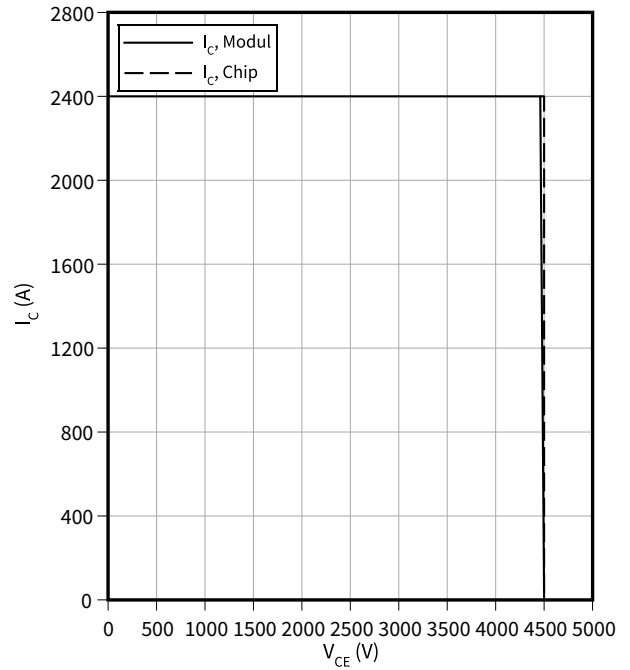
$I_C = 1200 \text{ A}, V_{GE} = \pm 15 \text{ V}, V_{CC} = 2800 \text{ V}$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

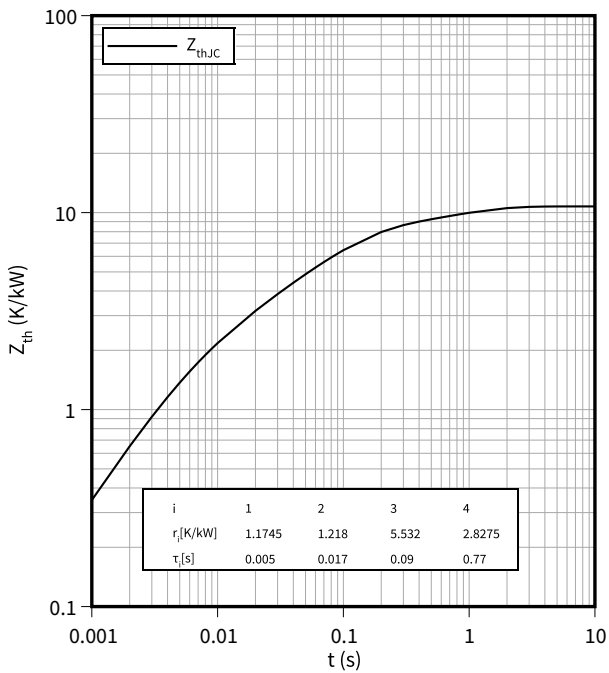
$I_C = f(V_{CE})$

$R_{Goff} = 7 \Omega, V_{GE} = \pm 15 \text{ V}, V_{CC} \leq 3000 \text{ V}, T_{vj} = 150 \text{ }^\circ\text{C}$



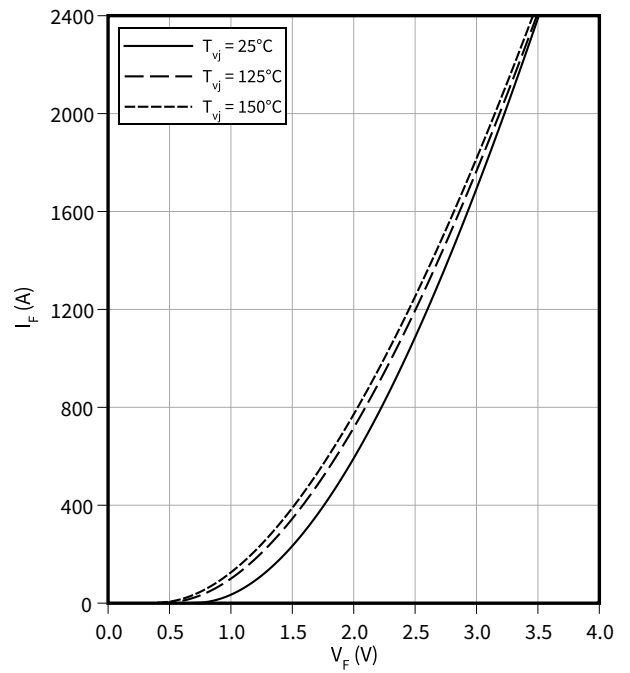
Transient thermal impedance, IGBT, Inverter

$Z_{th} = f(t)$



Forward characteristic (typical), Diode, Inverter

$I_F = f(V_F)$

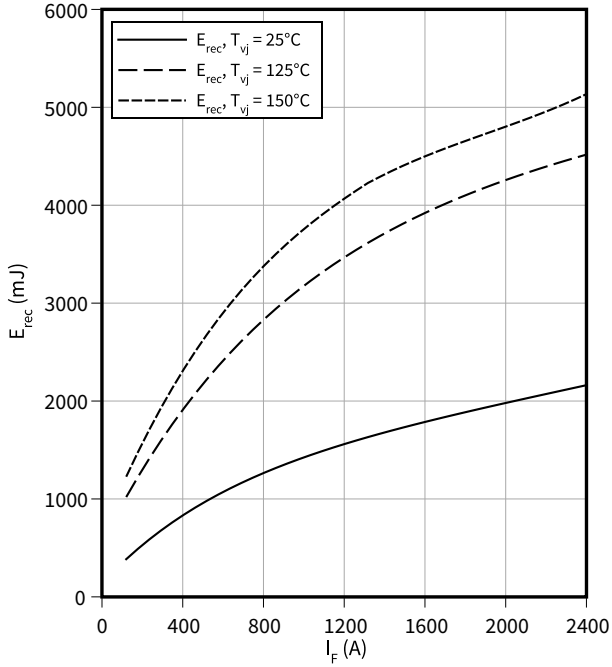


4 Characteristics diagrams

Switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

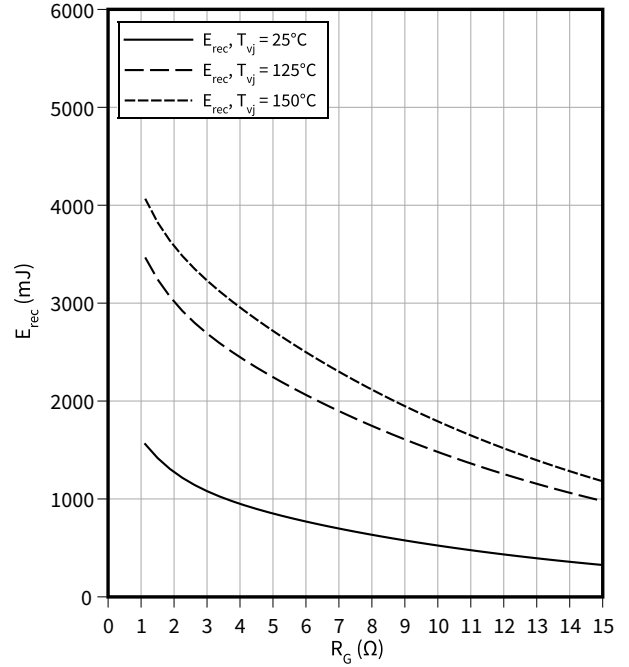
$V_{CE} = 2800\text{ V}$, $R_{Gon} = R_{Gon}(IGBT)$



Switching losses (typical), Diode, Inverter

$E_{rec} = f(R_G)$

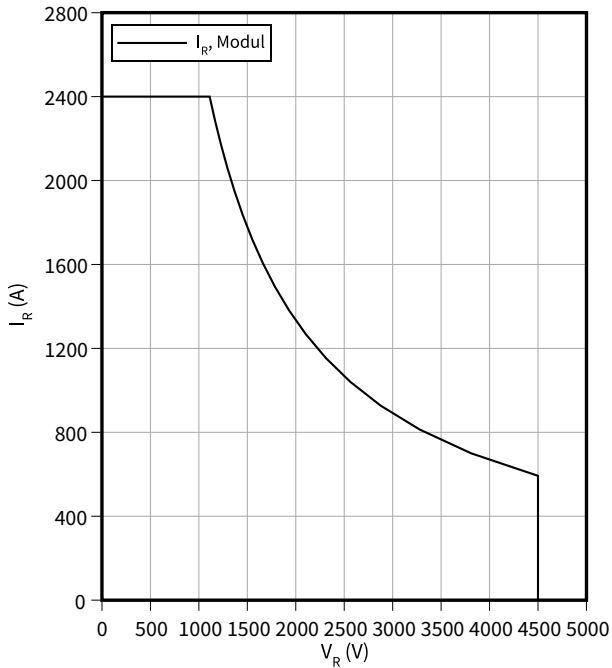
$V_{CE} = 2800\text{ V}$, $I_F = 1800\text{ A}$



Safe operating area (SOA), Diode, Inverter

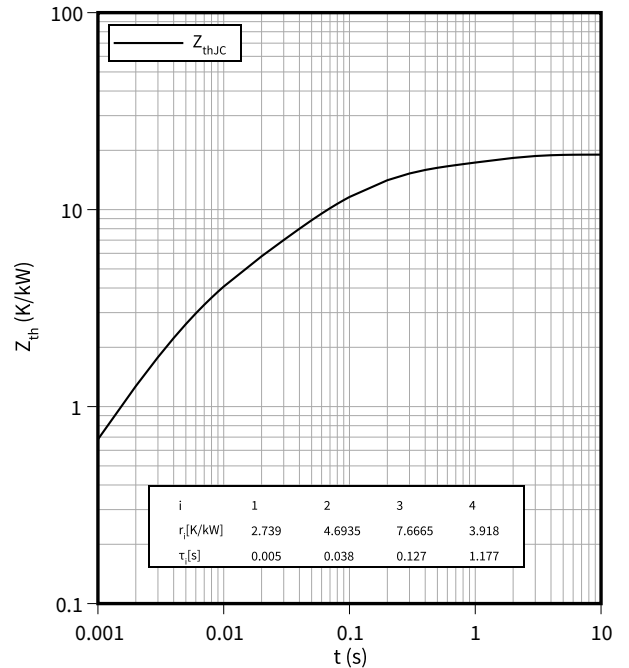
$I_R = f(V_R)$

$T_{vj} = 150\text{ °C}$



Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



5 Circuit diagram

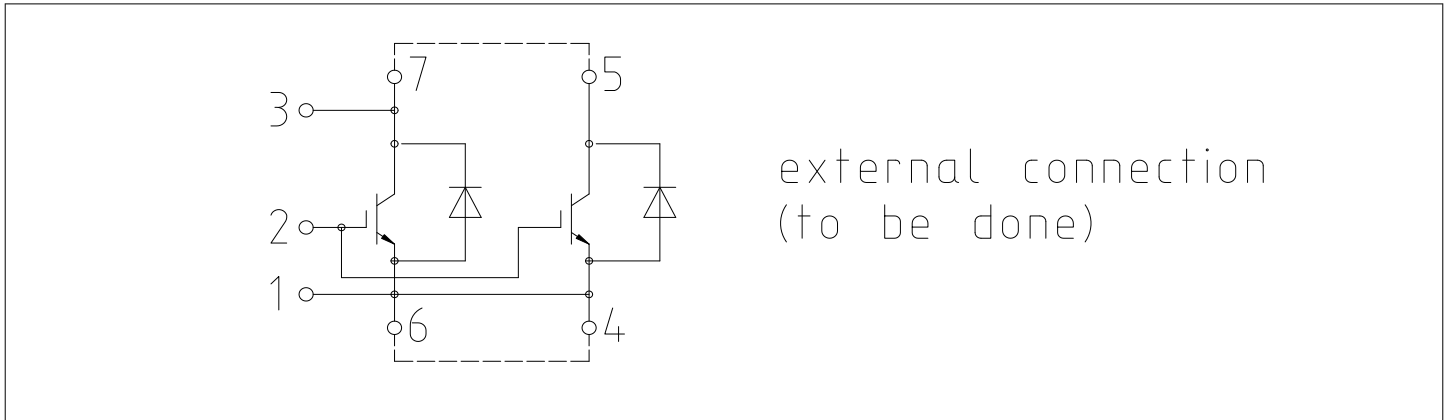


Figure 1

6 Package outlines

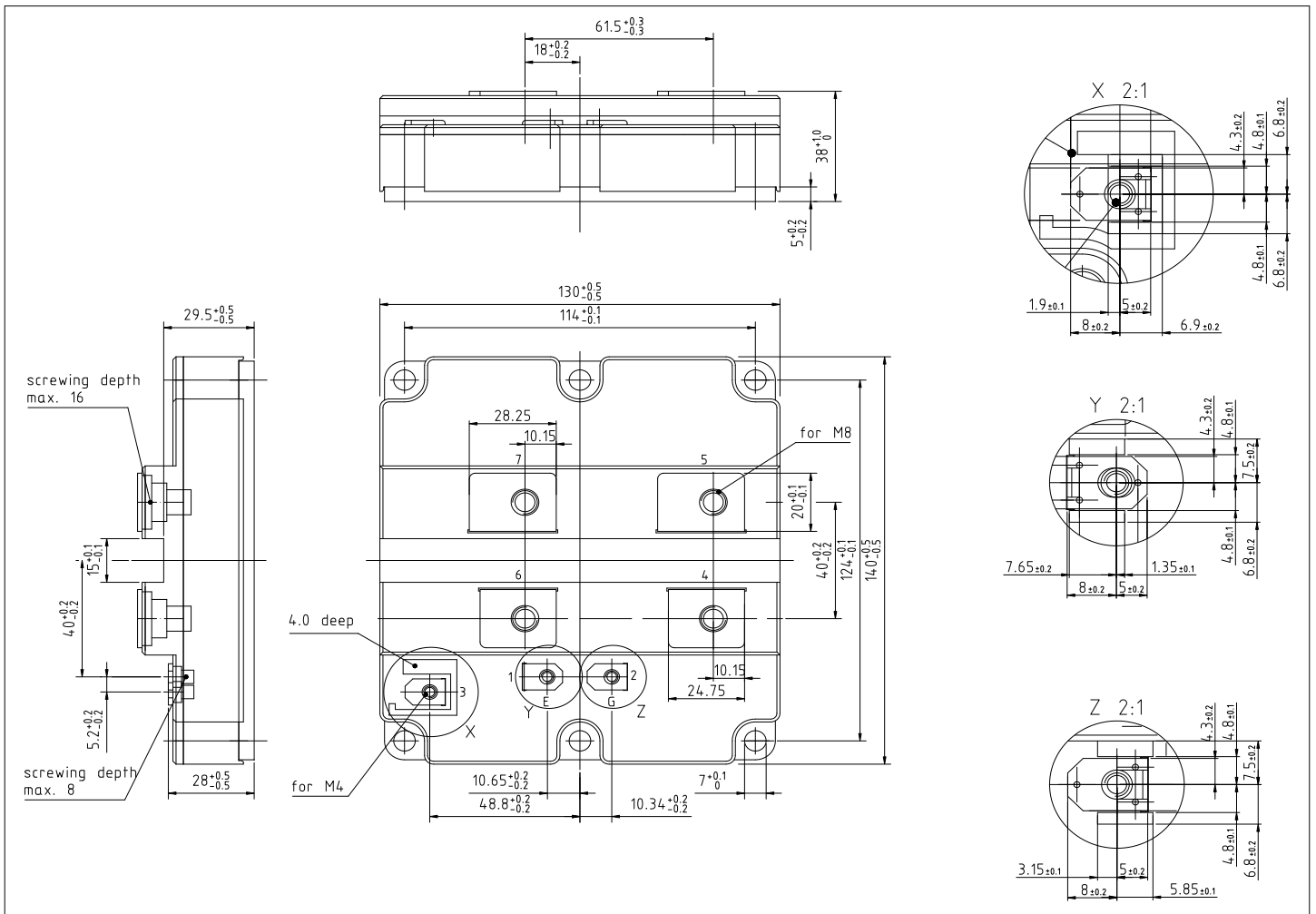


Figure 2

7 Module label code


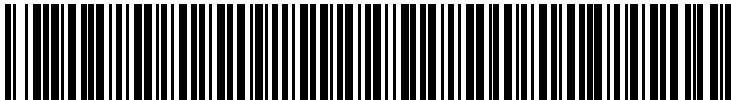
Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
0.10	2025-06-27	Target datasheet
0.20	2025-09-19	Preliminary datasheet
1.00	2025-10-17	Final datasheet

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